

Title (en)
SILICON DIOXIDE FILMS ON DIAMOND.

Title (de)
SILIZIUMDIOXIDFILME AUF DIAMANT.

Title (fr)
FILMS DE DIOXYDE DE SILICIUM SUR DIAMANT.

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EP 0417190 A1 19910320 (EN)

Application
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Priority
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Abstract (en)
[origin: WO8911897A1] A method for producing oriented diamond films on a substrate. Diamond seed crystals are suspended in a slurry (1) and applied to the substrate surface (2). Heating (3) the substrate removes the slurry fluid and produces seed crystals whose (111) crystal planes are substantially parallel to the plane of the substrate. An oriented polycrystalline diamond film may be grown about the seed crystals by CVD (4).

Abstract (fr)
On a mis point un procédé de production de films de diamant orientés sur un substrat. On suspend des germes de cristaux de diamant dans une bouillie (1) puis on les applique à la surface (2) du substrat. Le chauffage (3) du substrat élimine le fluide de la bouillie et produit des germes de cristaux dont les plans de cristaux (111) sont sensiblement parallèles au plan du substrat. On peut former par croissance un film de diamant polycristallin orienté autour des germes de cristaux par déposition chimique en phase vapeur (CVD) (4).

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